



## 1N60P

Power MOSFET

### 1.2A, 600V N-CHANNEL POWER MOSFET

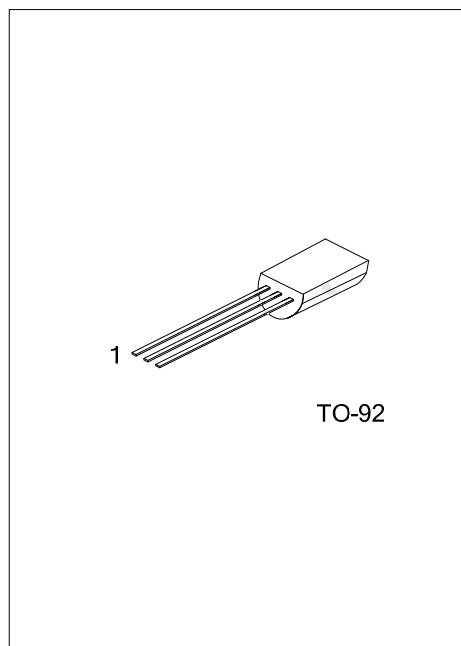
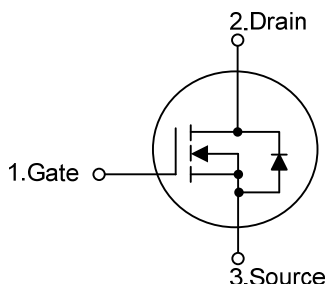
#### DESCRIPTION

The UTC **1N60P** is a high voltage power MOSFET and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and a high rugged avalanche characteristic. This power MOSFET is usually used at high speed switching applications of power supplies, PWM motor controls, high efficient DC to DC converters and bridge circuits.

#### FEATURES

- \*  $R_{DS(ON)} = 11.5\Omega @ V_{GS} = 10V$ .
- \* Ultra Low gate charge (typical 5.0nC)
- \* Low reverse transfer capacitance ( $C_{RSS} =$  typical 3.0 pF)
- \* Fast switching capability
- \* Avalanche energy specified
- \* Improved dv/dt capability, high ruggedness

#### SYMBOL



#### ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
1N60PL-T92-B	1N60PG-T92-B	TO-92	G	D	S	Tape Box
1N60PL-T92-K	1N60PG-T92-K	TO-92	G	D	S	Bulk
1N60PL-T92-R	1N60PG-T92-R	TO-92	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

<p>1N60PL-T92-B</p> <p>(1) Packing Type (2) Package Type (3) Lead Free</p>	<p>(1) B: Tape Box, K: Bulk, R: Tape Reel (2) T92: TO-92 (3) G: Halogen Free, L: Lead Free</p>
--	--

■ ABSOLUTE MAXIMUM RATINGS ( $T_C = 25^\circ\text{C}$ , unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Drain-Source Voltage	$V_{DSS}$	600	V
Gate-Source Voltage	$V_{GSS}$	$\pm 30$	V
Avalanche Current (Note 2)	$I_{AR}$	1.2	A
Continuous Drain Current	$I_D$	1.2	A
Pulsed Drain Current (Note 2)	$I_{DM}$	4.8	A
Avalanche Energy	Single Pulsed (Note 3)	$E_{AS}$	50
	Repetitive (Note 2)	$E_{AR}$	4.0
Peak Diode Recovery dv/dt (Note 4)	dv/dt	4.5	V/ns
Power Dissipation ( $T_A=25^\circ\text{C}$ )	$P_D$	1	W
Junction Temperature	$T_J$	+150	$^\circ\text{C}$
Operating Temperature	$T_{OPR}$	-55 ~ +150	$^\circ\text{C}$
Storage Temperature	$T_{STG}$	-55 ~ +150	$^\circ\text{C}$

- Notes:
1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
  2. Repetitive Rating: Pulse width limited by maximum junction temperature
  3.  $L = 60\text{mH}$ ,  $I_{AS} = 1\text{A}$ ,  $V_{DD} = 50\text{V}$ ,  $R_G = 25\Omega$ , Starting  $T_J = 25^\circ\text{C}$
  4.  $I_{SD} \leq 1.2\text{A}$ ,  $di/dt \leq 200\text{A}/\mu\text{s}$ ,  $V_{DD} \leq BV_{DSS}$ , Starting  $T_J = 25^\circ\text{C}$

■ THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	$\theta_{JA}$	140	$^\circ\text{C}/\text{W}$

■ ELECTRICAL CHARACTERISTICS (T<sub>C</sub>=25°C, unless otherwise specified.)

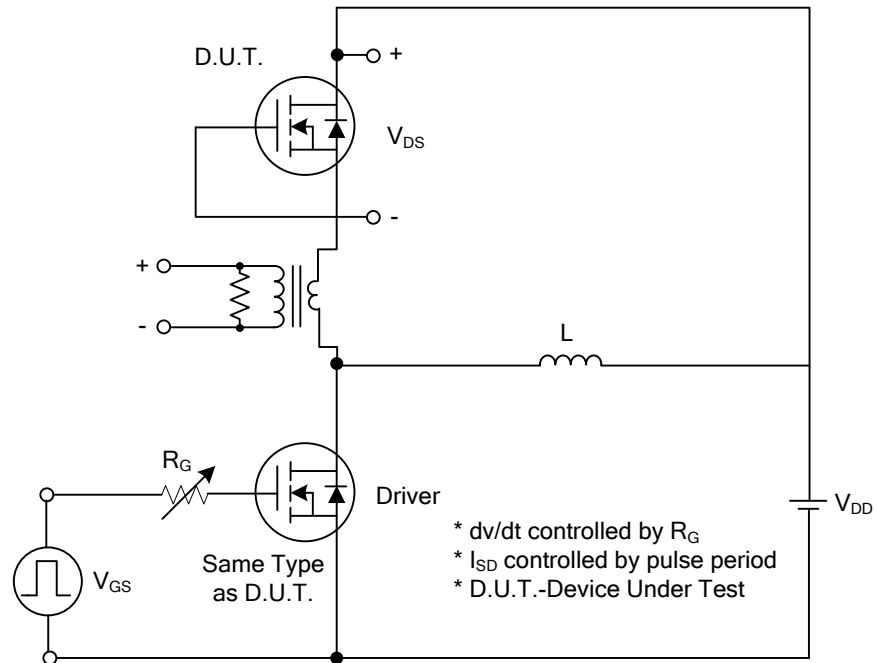
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
<b>OFF CHARACTERISTICS</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	600			V
Drain-Source Leakage Current	I <sub>DSS</sub>	V <sub>DS</sub> =600V, V <sub>GS</sub> =0V			10	μA
Gate-Source Leakage Current	Forward	I <sub>GSS</sub>			100	nA
	Reverse				-100	nA
Breakdown Voltage Temperature Coefficient	ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	I <sub>D</sub> =250μA		0.4		V/°C
<b>ON CHARACTERISTICS</b>						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	2.0		4.0	V
Static Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =0.6A		9.3	11.5	Ω
<b>DYNAMIC CHARACTERISTICS</b>						
Input Capacitance	C <sub>ISS</sub>	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V, f=1MHz		120	150	pF
Output Capacitance	C <sub>OSS</sub>			20	25	pF
Reverse Transfer Capacitance	C <sub>RSS</sub>			3.0	4.0	pF
<b>SWITCHING CHARACTERISTICS</b>						
Turn-On Delay Time	t <sub>D(ON)</sub>	V <sub>DD</sub> =300V, I <sub>D</sub> =1.2A, R <sub>G</sub> =50Ω (Note 2, 3)		5	20	ns
Turn-On Rise Time	t <sub>R</sub>			25	60	ns
Turn-Off Delay Time	t <sub>D(OFF)</sub>			7	25	ns
Turn-Off Fall Time	t <sub>F</sub>	V <sub>DS</sub> =480V, V <sub>GS</sub> =10V, I <sub>D</sub> =1.2A (Note 2, 3)		25	60	ns
Total Gate Charge	Q <sub>G</sub>			5.0	6.0	nC
Gate-Source Charge	Q <sub>GS</sub>			1.0		nC
Gate-Drain Charge	Q <sub>GD</sub>		2.6		nC	
<b>SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS</b>						
Drain-Source Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =1.2A			1.4	V
Maximum Continuous Drain-Source Diode Forward Current	I <sub>S</sub>				1.2	A
Maximum Pulsed Drain-Source Diode Forward Current	I <sub>SM</sub>				4.8	A
Reverse Recovery Time	t <sub>rr</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =1.2A		160		ns
Reverse Recovery Charge	Q <sub>RR</sub>	dI <sub>F</sub> /dt=100A/μs (Note 1)		0.3		μC

Notes: 1. Repetitive Rating: Pulse width limited by maximum junction temperature

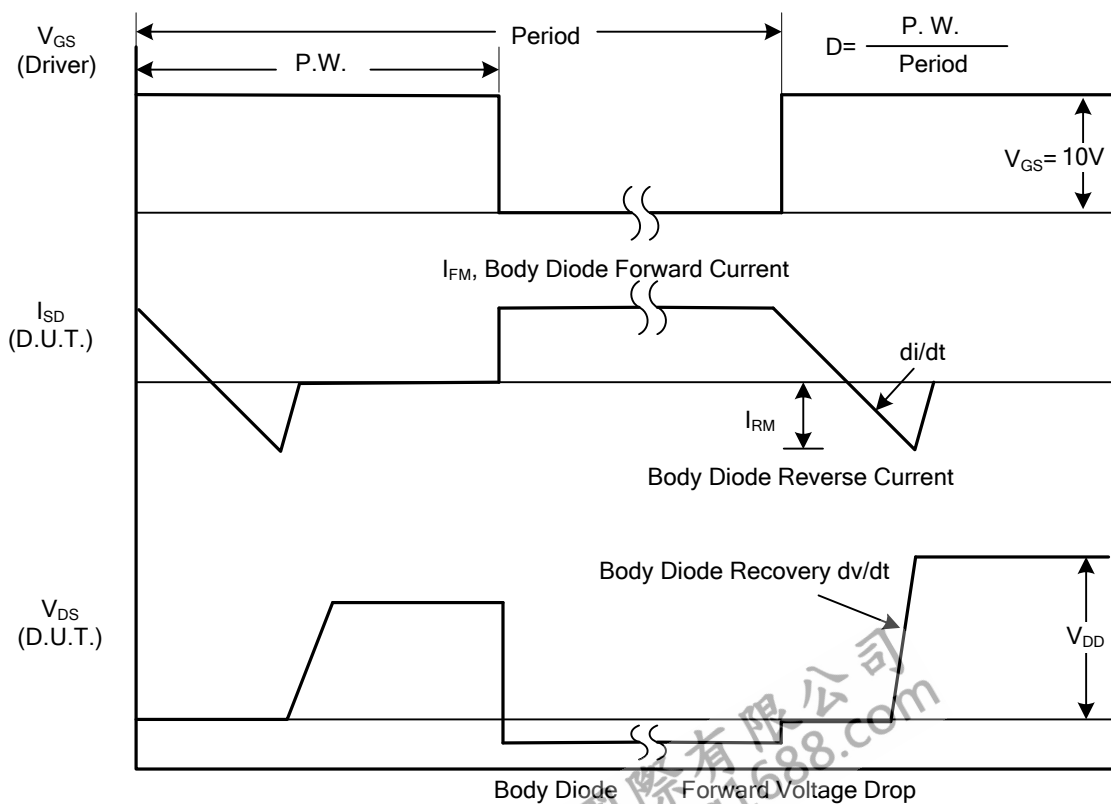
2. Pulse Test: Pulse Width ≤300μs, Duty Cycle ≤2%

3. Essentially Independent of Operating Temperature

### TEST CIRCUITS AND WAVEFORMS

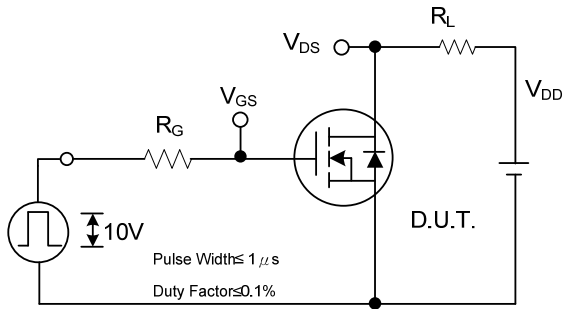


Peak Diode Recovery  $dv/dt$  Test Circuit

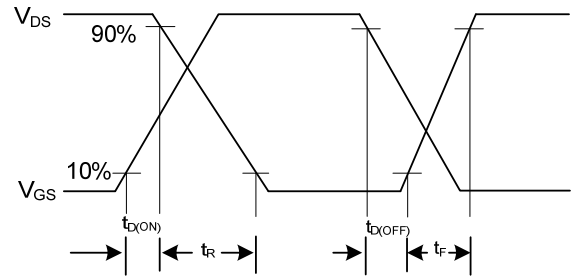


Peak Diode Recovery  $dv/dt$  Waveforms

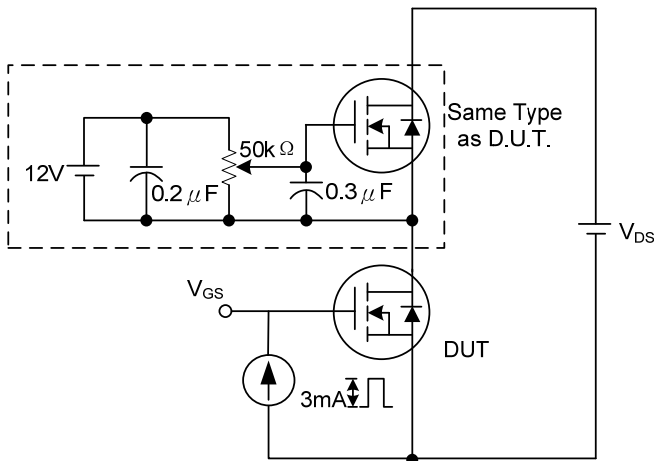
### TEST CIRCUITS AND WAVEFORMS (Cont.)



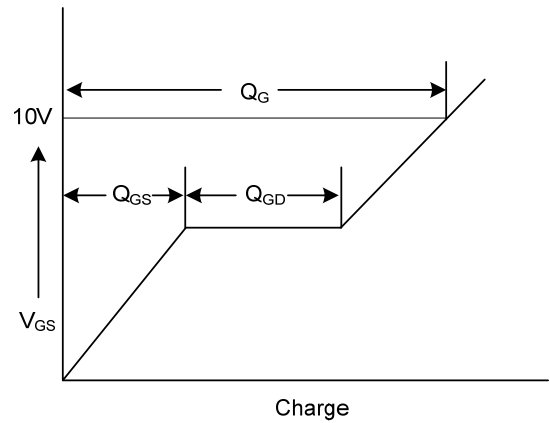
Switching Test Circuit



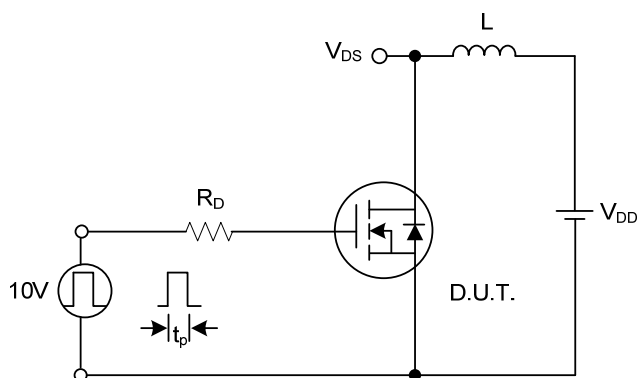
Switching Waveforms



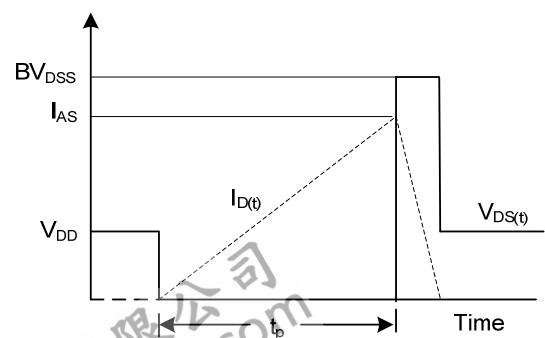
Gate Charge Test Circuit



Gate Charge Waveform

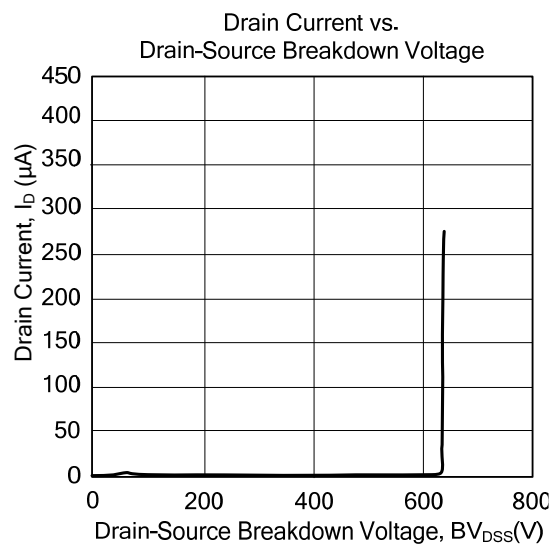
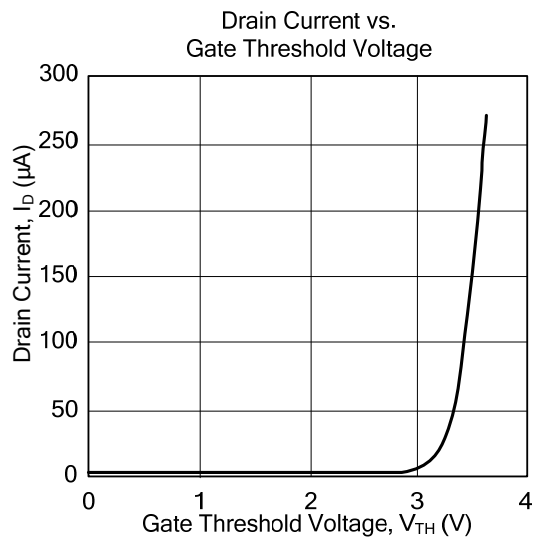
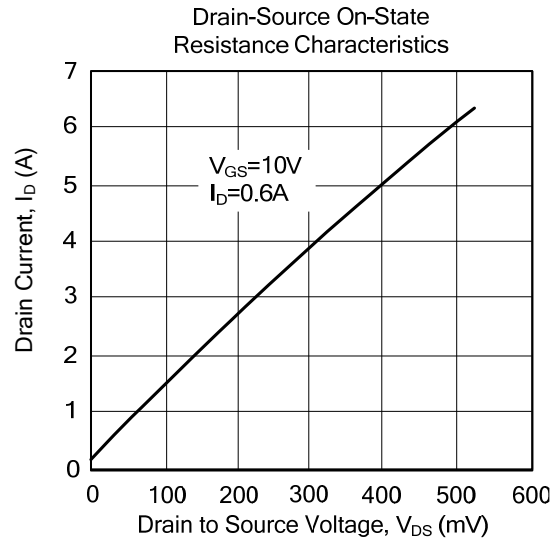
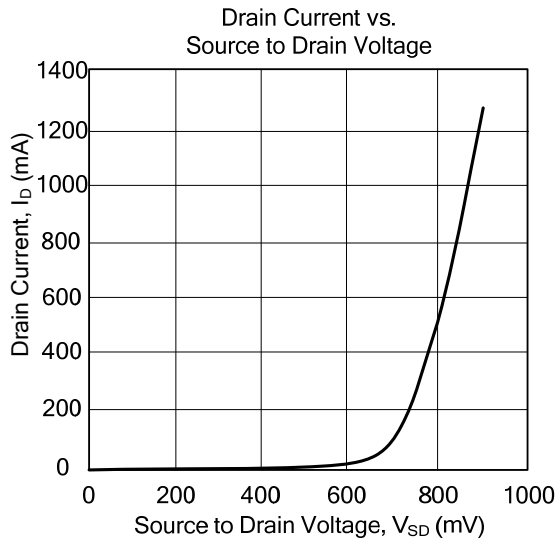


Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

### TYPICAL CHARACTERISTICS



UTC assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all UTC products described or contained herein. UTC products are not designed for use in life support appliances, devices or systems where malfunction of these products can be reasonably expected to result in personal injury. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner. The information presented in this document does not form part of any quotation or contract, is believed to be accurate and reliable and may be changed without notice.